BAS16HT1

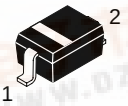
Preferred Device

Switching Diode

ON Semiconductor®

http://onsemi.com

1 CATHODE — 2 ANODE



SOD−323
CASE 477
STYLE 1

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Continuous Reverse Voltage	V_R	75	Vdc
Peak Forward Current	I_F	200	mAdc
Peak Forward Surge Current	$I_{FM(surge)}$	500	mAdc

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board (Note 1) T_A = 25°C Derate above 25°C	P_D	200 1.57	mW mW/°C
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	635	°C/W
Junction and Storage Temperature	T_J, T_{stg}	−55 to 150	°C

1. FR-4 Minimum Pad.

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Reverse Voltage Leakage Current (V_R = 75 Vdc) (V_R = 75 Vdc, T_J = 150°C) (V_R = 25 Vdc, T_J = 150°C)	I_R	 − − −	 1.0 50 30	µAdc
Reverse Breakdown Voltage (I_{BR} = 100 µAdc)	$V_{(BR)}$	75	−	Vdc
Forward Voltage (I_F = 1.0 mAdc) (I_F = 10 mAdc) (I_F = 50 mAdc) (I_F = 150 mAdc)	V_F	 − − − −	 715 855 1000 1250	mV
Diode Capacitance (V_R = 0, f = 1.0 MHz)	C_D	−	2.0	pF
Forward Recovery Voltage (I_F = 10 mAdc, t_r = 20 ns)	V_{FR}	−	1.75	Vdc
Reverse Recovery Time (I_F = I_R = 10 mAdc, R_L = 50 Ω)	t_{rr}	−	6.0	ns
Stored Charge (I_F = 10 mAdc to V_R = 5.0 Vdc, R_L = 500 Ω)	Q_S	−	45	pC

MARKING DIAGRAM

A6 = Specific Device Code
M = Date Code

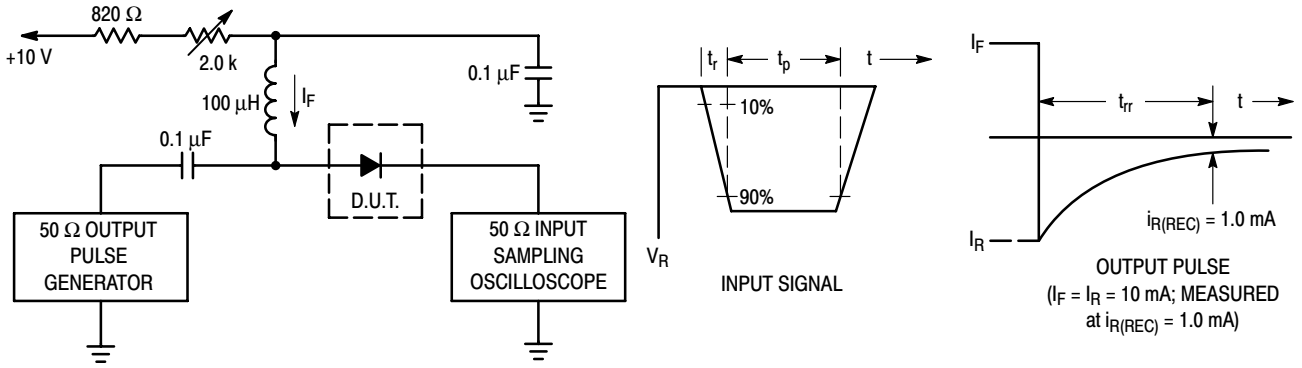
ORDERING INFORMATION

Device	Package	Shipping†
BAS16HT1	SOD−323	3000/Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

Preferred devices are recommended choices for future use and best overall value.

Publication Order Number:



Notes: 1. A 2.0 kΩ variable resistor adjusted for a Forward Current (I_F) of 10 mA.
2. Input pulse is adjusted so $I_{R(peak)}$ is equal to 10 mA.
3. $t_p \gg t_{rr}$

Figure 1. Recovery Time Equivalent Test Circuit

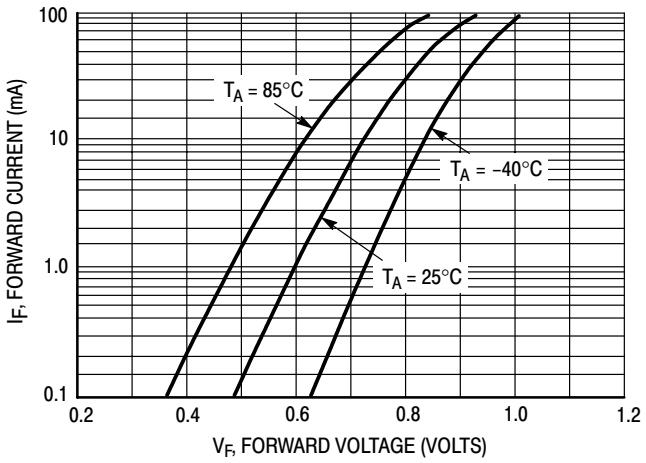


Figure 2. Forward Voltage

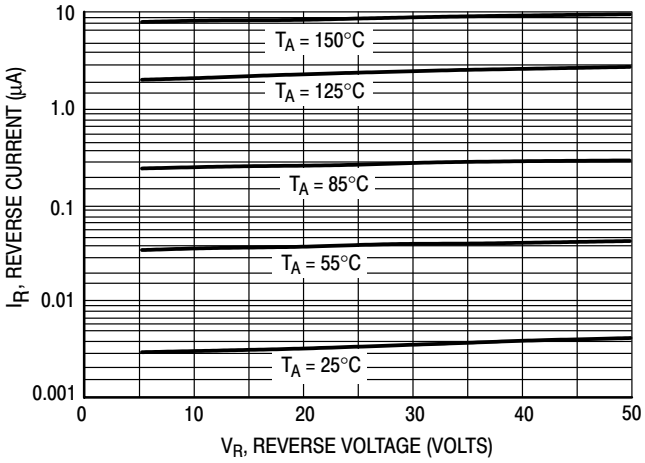


Figure 3. Leakage Current

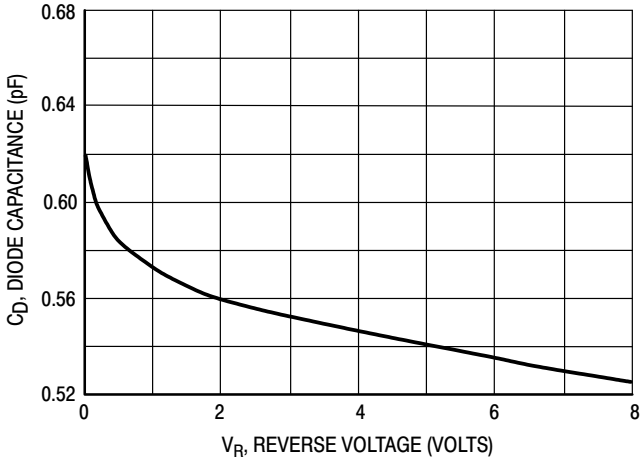


Figure 4. Capacitance

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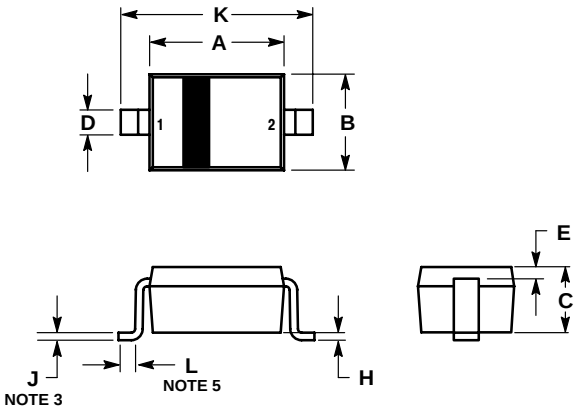
PACKAGE DIMENSIONS

SOD−323
CASE 477−02
ISSUE D

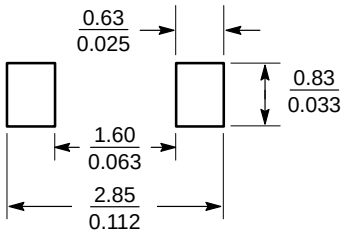


NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. LEAD THICKNESS SPECIFIED PER L/F DRAWING WITH SOLDER PLATING.
4. DIMENSIONS A AND B DO NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS.
5. DIMENSION L IS MEASURED FROM END OF RADIUS.

	MILLIMETERS		INCHES	
DIM	MIN	MAX	MIN	MAX
A	1.60	1.80	0.063	0.071
B	1.15	1.35	0.045	0.053
C	0.80	1.00	0.031	0.039
D	0.25	0.40	0.010	0.016
E	0.15 REF		0.006 REF	
H	0.00	0.10	0.000	0.004
J	0.089	0.177	0.0035	0.0070
K	2.30	2.70	0.091	0.106
L	0.075	−−−	0.003	−−−

STYLE 1:
PIN 1. CATHODE
2. ANODE

SOLDERING FOOTPRINT*



*For additional information on our Pb−Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT:
Literature Distribution Center for ON Semiconductor
P.O. Box 5163, Denver, Colorado 80217 USA
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For additional information, please contact your local Sales Representative.

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